

2SD2195 / 2SD1980 / 2SD1867 / 2SD2398

- 1) Darlington connection for high DC current gain.
- 2) Built-in resistor between base and emitter.
- 3) Built-in damper diode.
- 4) Complements the 2SB1580 / 2SB1316 / 2SB1567.

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	100	V
Collector-emitter voltage	V_{CEO}	100	V
Emitter-base voltage	V_{BE0}	6	V
Collector current	I_C	2	A(DC)
		3	A(Pulse) *1
		2	W *2
Collector power dissipation	P_C	1	W(T _C =25°C)
		10	
		1	W *3
		2	
		20	W(T _C =25°C)
Junction temperature	T_{Jj}	150	°C
Storage temperature	T_{Stg}	-55 ~ +150	°C

- | Type | 2SD2195 | 2SD1980 | 2SD1867 | 2SD2398 |
|------------------------------|----------|----------|----------|----------|
| Package | MPT3 | CPT3 | ATV | TO-220FN |
| hfe | 1k ~ 10k | 1k ~ 10k | 1k ~ 10k | 1k ~ 10k |
| Marking | DP * | - | - | - |
| Code | T100 | TL | TV2 | - |
| Basic ordering unit (pieces) | 1000 | 2500 | 2500 | 500 |

$R_1 \approx 3.5k\Omega$ B : Base
 $R_2 \approx 300\Omega$ C : Collector
 E : Emitter

Technical drawing of the BQHM-MPT3 connector showing dimensions in millimeters:

- Overall length: 40
- Pin spacing (center-to-center): 25
- Pin diameter: 1.5
- Pin thickness: 0.4
- Pin height from base: 1.5
- Base width: 1.8
- Base thickness: 1.5
- Mounting hole diameter: 4.4

Figure 1: Taping specifications for the 2N4350 JFET. The diagram shows three views of the component: (1) Emitter, (2) Collector, and (3) Base. Dimensions are given in millimeters. The emitter view shows a width of 6.8 mm, a height of 0.65 mm (max), and a distance of 1.0 mm between the emitter and collector. The collector view shows a width of 2.5 mm, a height of 0.45 mm, and a distance of 1.0 mm between the collector and base. The base view shows a width of 14.5 mm, a height of 0.5 mm, and a distance of 0.9 mm between the base and emitter. The base is also labeled with dimensions 2.54 mm and 2.54 mm.

Taping specifications (3) Base

(1) Base/Gate
(2) Collector/Drain
(3) Emitter/Source

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{ceo}	100	—	—	V	I _c = 50 μA
Collector-emitter breakdown voltage	BV _{ceo}	100	—	—	V	I _c = 5 mA
Collector cutoff current	I _{ceo}	—	—	10	μA	V _{ceo} = 100V
Emitter cutoff current	I _{eco}	—	—	3	mA	V _{be} = 5V
Collector-emitter saturation voltage	V _{CE(sat)}	—	1.5	—	V	I _b = 1A, I _c = 1mA
DC current transfer ratio	h _{FE}	1000	—	10000	—	V _{CE} = 20V, I _c = 1A
Output capacitance	C _{ob}	—	25	—	pF	V _{CE} = 10V, I _c = 0A, f = 1MHz

- Measured using pulse current.

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